NSN 5961-00-068-8231

Thyristor Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-00-068-8231 **Inclosure Material:** Metal **Overall Length:** 0.505 inches **Overall Diameter:** 0.650 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 400.0 breakover voltage, dc **Current Rating Per Characteristic:** 18.00 amperes source cutoff current **Power Rating Per Characteristic:** 0.5 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Internal junction configuration arrangement pnpn **Thread Series Designator: Terminal Type And Quantity:** 1 threaded stud and 2 solder stud **Specification Data:** 80131-release3681 professional/industrial association specification Shelf Life: N/a **Unit Of Measure: Demilitarization:**

No

NSN 5961-00-068-8231

Thyristor Semiconductor Device - Page 2 of 2



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